International
IOR Rectifier

PD- 91577B

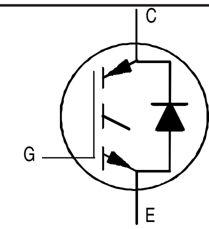
IRG4PH40KD

INSULATED GATE BIPOLAR TRANSISTOR WITH ULTRAFAST SOFT RECOVERY DIODE

Short Circuit Rated
UltraFast IGBT

Features

- High short circuit rating optimized for motor control, t_{sc} =10µs, V_{CC} = 720V , T_J = 125°C, V_{GE} = 15V
- Combines low conduction losses with high switching speed
- Tighter parameter distribution and higher efficiency than previous generations
- IGBT co-packaged with HEXFRED™ ultrafast, ultrasoft recovery antiparallel diodes



n-channel

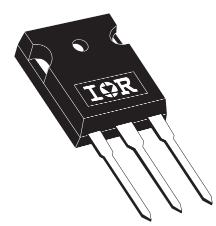
V_{CES} = 1200V

$V_{CE(on)\ typ.}$ = 2.74V

@V_{GE} = 15V, I_C = 15A

Benefits

- Latest generation 4 IGBT's offer highest power density motor controls possible
- HEXFRED™ diodes optimized for performance with IGBTs. Minimized recovery characteristics reduce noise, EMI and switching losses
- This part replaces the IRGPH40KD2 and IRGPH40MD2 products
- For hints see design tip 97003


TO-247AC

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	1200	V
I_C @ T_C = 25°C	Continuous Collector Current	30	A
I_C @ T_C = 100°C	Continuous Collector Current	15	
I_{CM}	Pulsed Collector Current ①	60	
I_{LM}	Clamped Inductive Load Current ②	60	
I_F @ T_C = 100°C	Diode Continuous Forward Current	8.0	
I_{FM}	Diode Maximum Forward Current	130	
t_{sc}	Short Circuit Withstand Time	10	µs
V_{GE}	Gate-to-Emitter Voltage	± 20	V
P_D @ T_C = 25°C	Maximum Power Dissipation	160	W
P_D @ T_C = 100°C	Maximum Power Dissipation	65	
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +150	°C
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	
	Mounting Torque, 6-32 or M3 Screw.	10 lbf•in (1.1 N•m)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case - IGBT	–––	–––	0.77	°C/W
$R_{\theta JC}$	Junction-to-Case - Diode	–––	–––	1.7	
$R_{\theta CS}$	Case-to-Sink, flat, greased surface	–––	0.24	–––	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	–––	–––	40	
Wt	Weight	–––	6 (0.21)	–––	g (oz)

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage③	1200	—	—	V	V_{GE} = 0V, I_C = 250µA
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.37	—	V/°C	V_{GE} = 0V, I_C = 1.0mA
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	—	2.74	3.4	V	I_C = 15A; V_{GE} = 15V
		—	3.29	—		I_C = 30A; See Fig. 2, 5
		—	2.53	—		I_C = 15A, T_J = 150°C
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	6.0		V_{CE} = V_{GE}, I_C = 250µA
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	—	-3.3	—	mV/°C	V_{CE} = V_{GE}, I_C = 250µA
g_{fe}	Forward Transconductance ④	8.0	12	—	S	V_{CE} = 100V, I_C = 15A
I_{CES}	Zero Gate Voltage Collector Current	—	—	250	µA	V_{GE} = 0V, V_{CE} = 1200V
		—	—	3000		V_{GE} = 0V, V_{CE} = 1200V, T_J = 150°C
V_{FM}	Diode Forward Voltage Drop	—	2.6	3.3	V	I_C = 8.0A; See Fig. 13
		—	2.4	3.1		I_C = 8.0A, T_J = 125°C
I_{GES}	Gate-to-Emitter Leakage Current	—	—	±100	nA	V_{GE} = ±20V

Switching Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions	
Q_g	Total Gate Charge (turn-on)	—	94	140	nC	I_C = 15A	
Q_{ge}	Gate - Emitter Charge (turn-on)	—	14	22		V_{CC} = 400V See Fig.8	
Q_{gc}	Gate - Collector Charge (turn-on)	—	37	55		V_{GE} = 15V	
$t_{d(on)}$	Turn-On Delay Time	—	50	—	ns		
t_r	Rise Time	—	31	—		T_J = 25°C	
$t_{d(off)}$	Turn-Off Delay Time	—	96	140		I_C = 15A, V_{CC} = 800V	
t_f	Fall Time	—	220	330		V_{GE} = 15V, R_G = 10Ω	
E_{on}	Turn-On Switching Loss	—	1.31	—	mJ	Energy losses include "tail"	
E_{off}	Turn-Off Switching Loss	—	1.12	—		and diode reverse recovery	
E_{ts}	Total Switching Loss	—	2.43	2.8		See Fig. 9,10,18	
t_{sc}	Short Circuit Withstand Time	10	—	—	µs	V_{CC} = 720V, T_J = 125°C V_{GE} = 15V, R_G = 10Ω , V_{CPK} < 500V	
$t_{d(on)}$	Turn-On Delay Time	—	49	—	ns	T_J = 150°C, See Fig. 10,11,18	
t_r	Rise Time	—	33	—		I_C = 15A, V_{CC} = 800V	
$t_{d(off)}$	Turn-Off Delay Time	—	290	—		V_{GE} = 15V, R_G = 10Ω,	
t_f	Fall Time	—	440	—		Energy losses include "tail"	
E_{ts}	Total Switching Loss	—	5.1	—	mJ	and diode reverse recovery	
L_E	Internal Emitter Inductance	—	13	—	nH	Measured 5mm from package	
C_{ies}	Input Capacitance	—	1600	—	pF	V_{GE} = 0V	
C_{oes}	Output Capacitance	—	77	—		V_{CC} = 30V See Fig. 7	
C_{res}	Reverse Transfer Capacitance	—	26	—		f = 1.0MHz	
t_{rr}	Diode Reverse Recovery Time	—	63	95	ns	T_J = 25°C See Fig.	
		—	106	160		T_J = 125°C 14	I_F = 8.0A
I_{rr}	Diode Peak Reverse Recovery Current	—	4.5	8.0	A	T_J = 25°C See Fig.	
		—	6.2	11		T_J = 125°C 15	V_R = 200V
Q_{rr}	Diode Reverse Recovery Charge	—	140	380	nC	T_J = 25°C See Fig.	
		—	335	880		T_J = 125°C 16	di/dt = 200Aµs
$di_{(rec)M}/dt$	Diode Peak Rate of Fall of Recovery	—	133	—	A/µs	T_J = 25°C See Fig.	
	During t_b	—	85	—		T_J = 125°C 17	

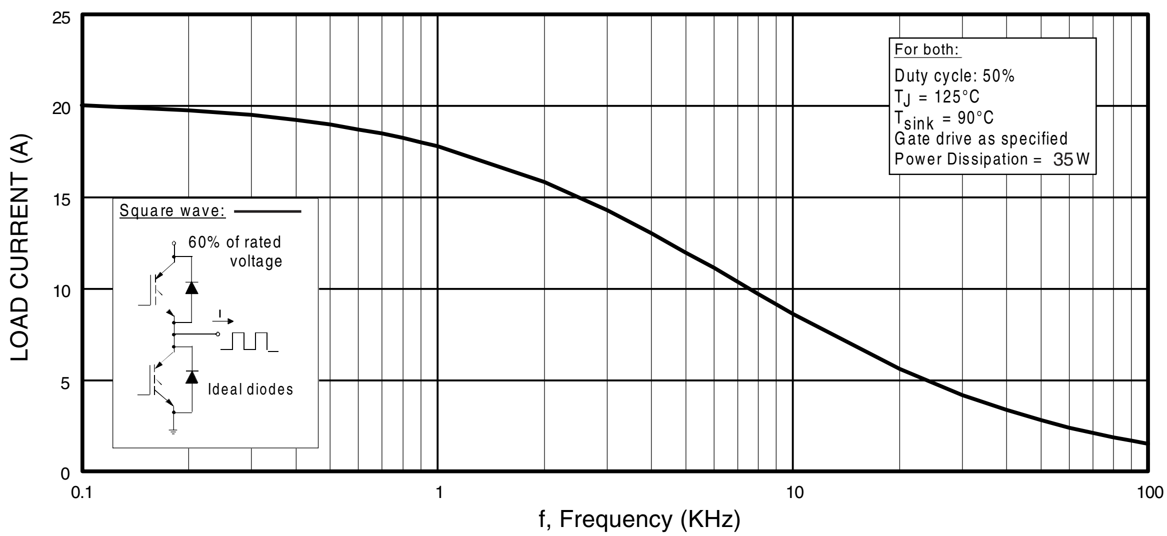


Fig. 1 - Typical Load Current vs. Frequency
(Load Current = I_{RMS} of fundamental)

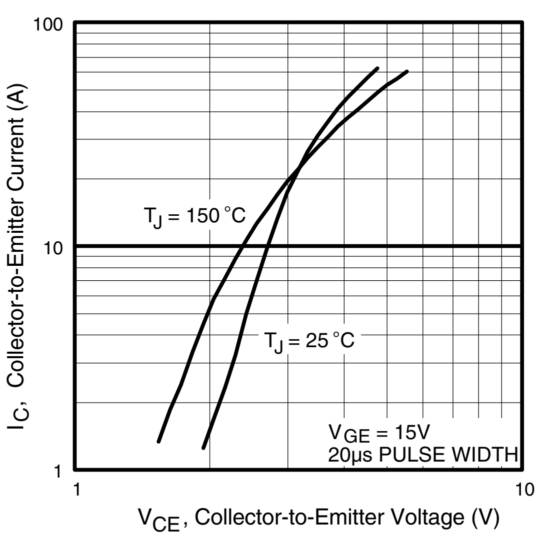


Fig. 2 - Typical Output Characteristics

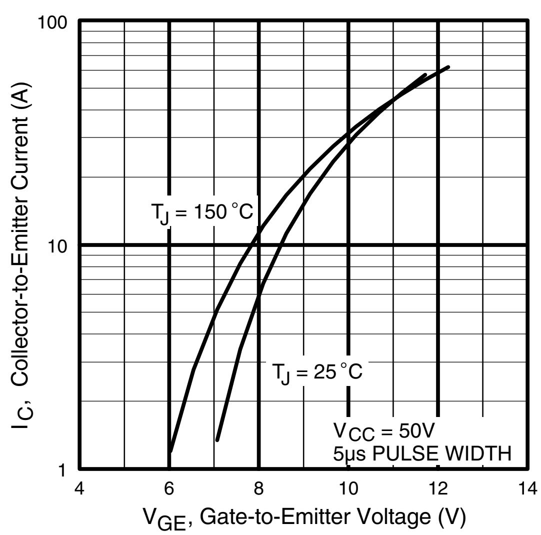


Fig. 3 - Typical Transfer Characteristics

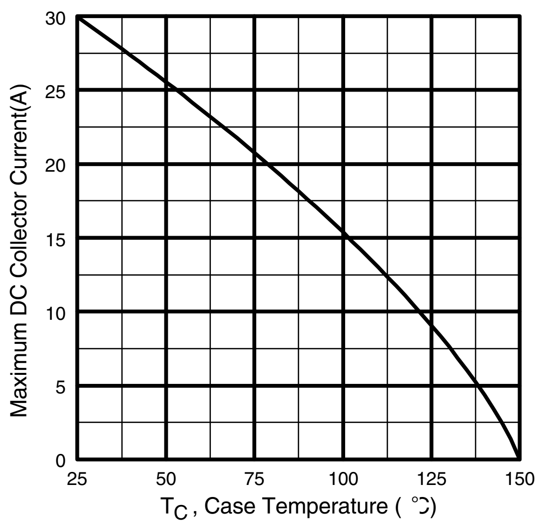


Fig. 4 - Maximum Collector Current vs. Case Temperature

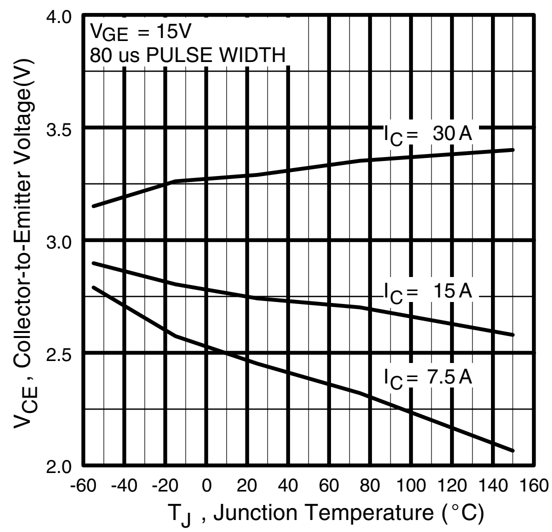


Fig. 5 - Typical Collector-to-Emitter Voltage vs. Junction Temperature

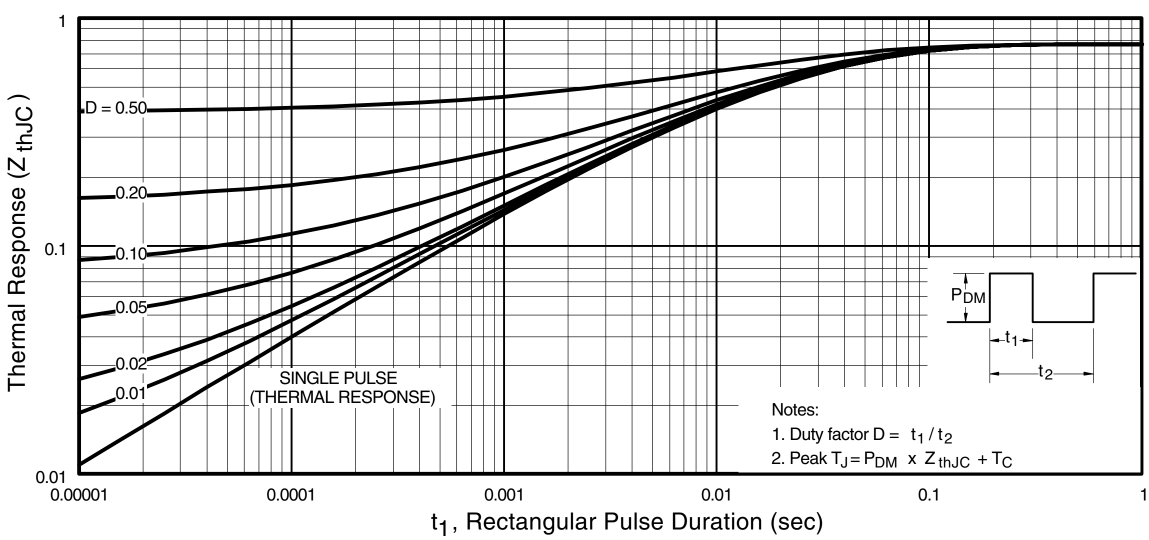


Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

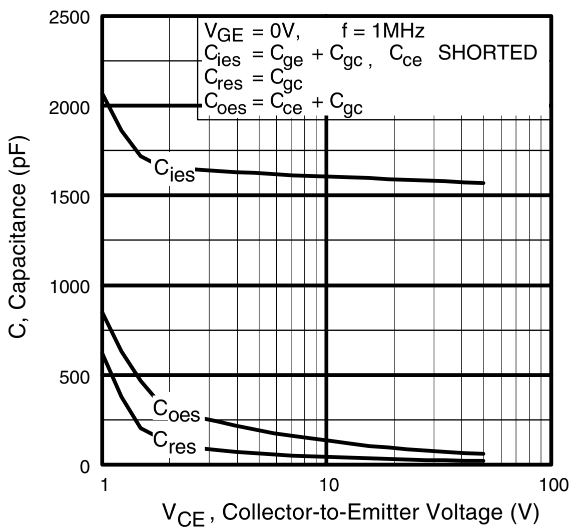


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

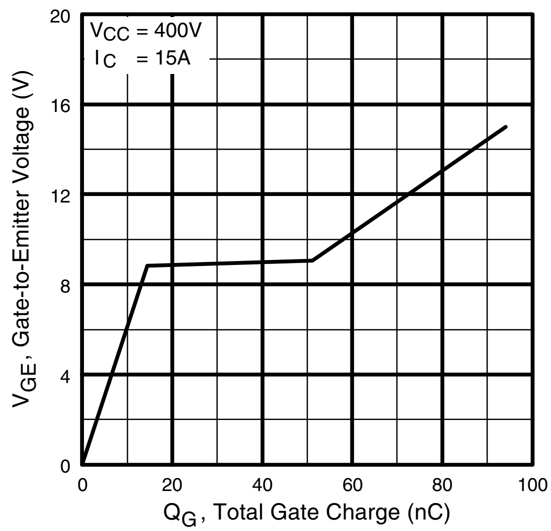


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

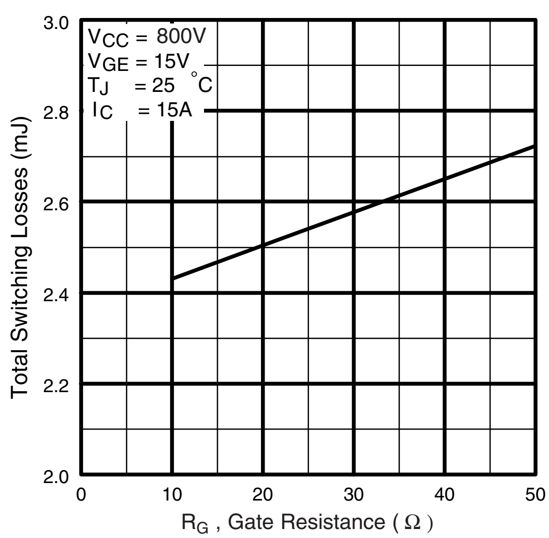


Fig. 9 - Typical Switching Losses vs. Gate Resistance

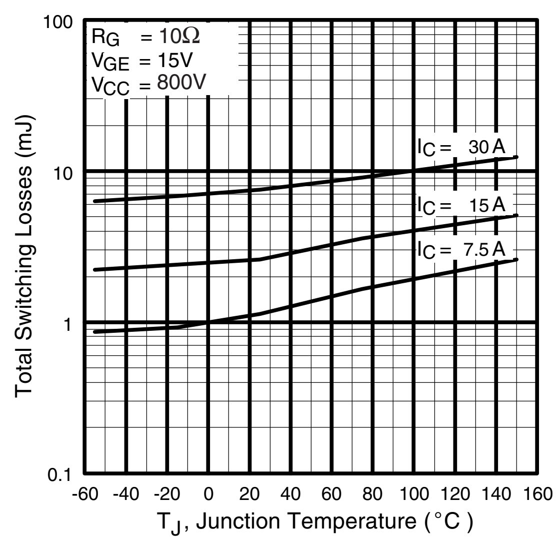


Fig. 10 - Typical Switching Losses vs. Junction Temperature

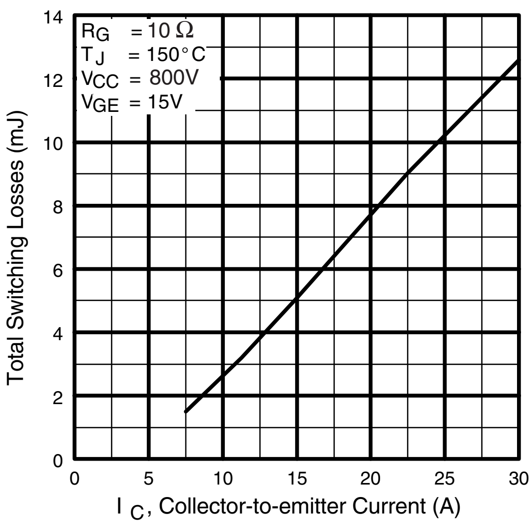


Fig. 11 - Typical Switching Losses vs. Collector-to-Emitter Current

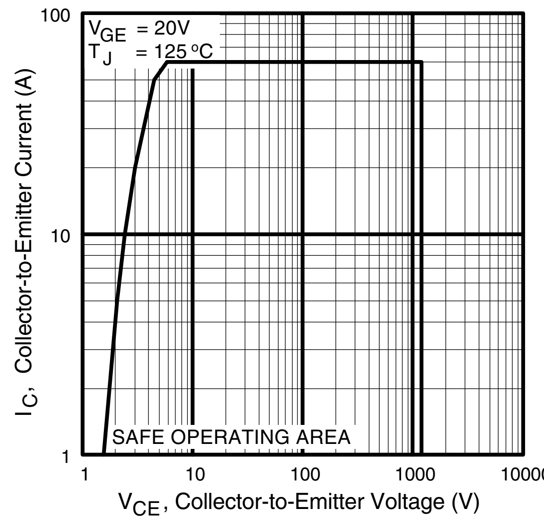


Fig. 12 - Turn-Off SOA

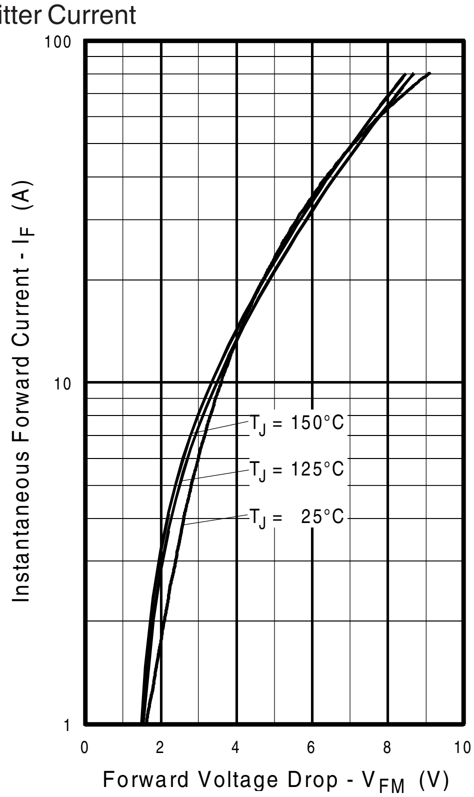


Fig. 13 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

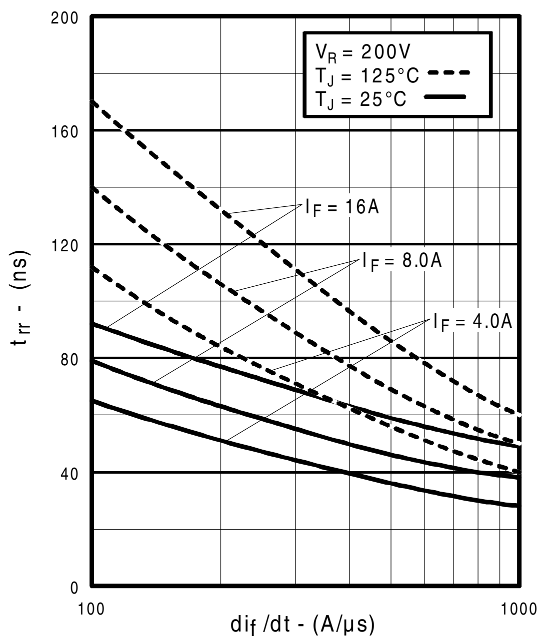


Fig. 14 - Typical Reverse Recovery vs. di_f/dt

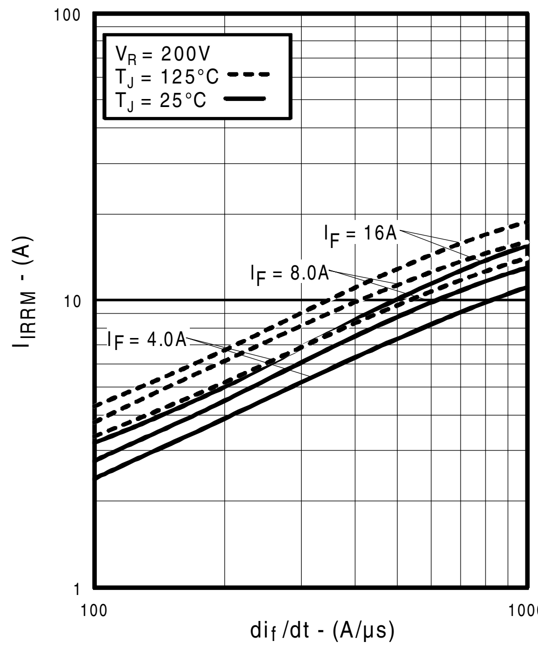


Fig. 15 - Typical Recovery Current vs. di_f/dt

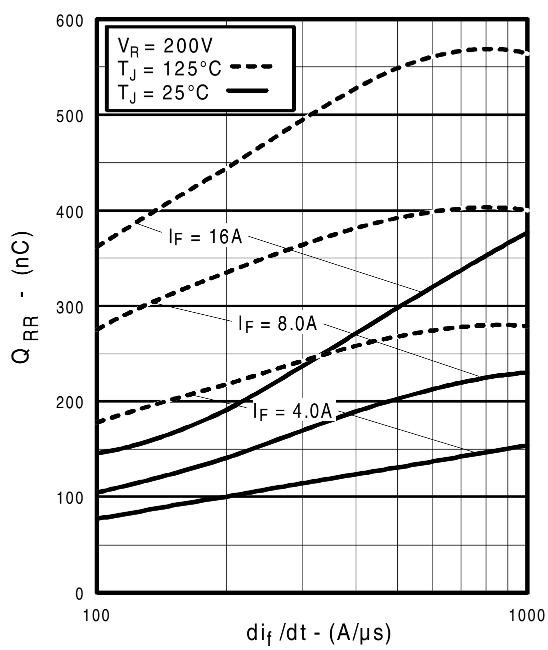


Fig. 16 - Typical Stored Charge vs. di_f/dt

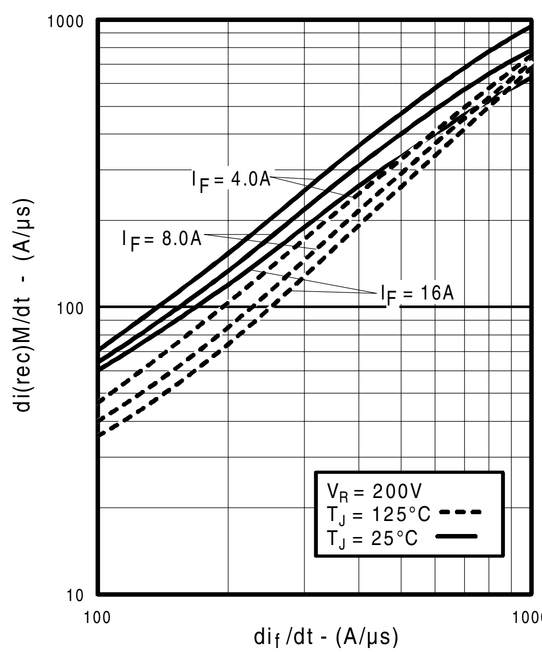


Fig. 17 - Typical $di_{(rec)M}/dt$ vs. di_f/dt

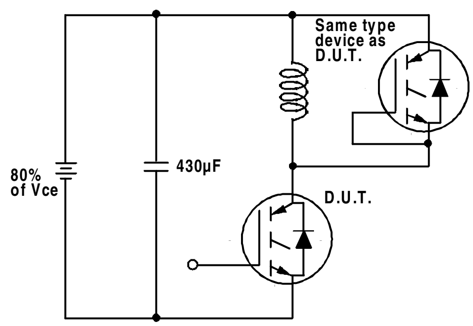


Fig. 18a - Test Circuit for Measurement of I_{LM}, E_{on}, $E_{off(diode)}$, t_{rr}, Q_{rr}, I_{rr}, $t_{d(on)}$, t_r, $t_{d(off)}$, t_f

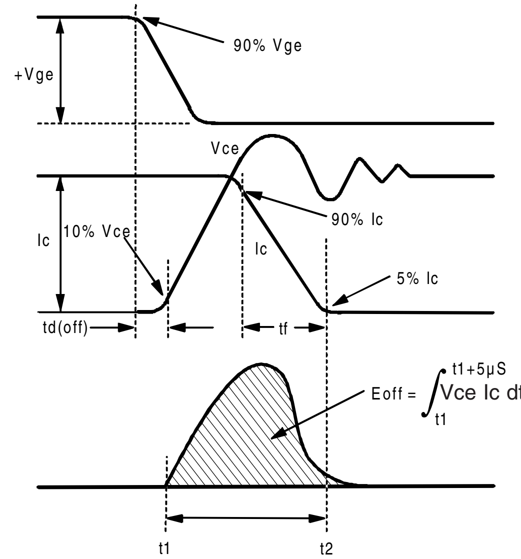


Fig. 18b - Test Waveforms for Circuit of Fig. 18a, Defining E_{off}, $t_{d(off)}$, t_f

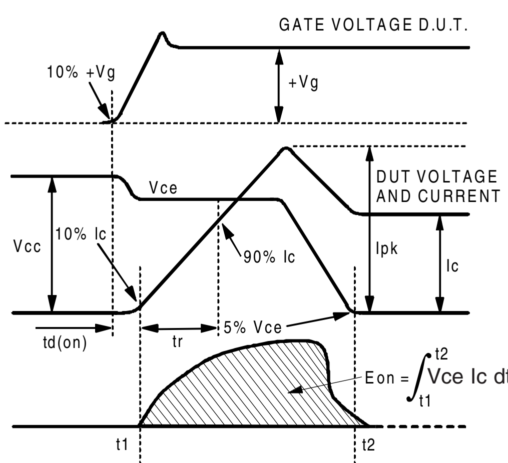


Fig. 18c - Test Waveforms for Circuit of Fig. 18a, Defining E_{on}, $t_{d(on)}$, t_r

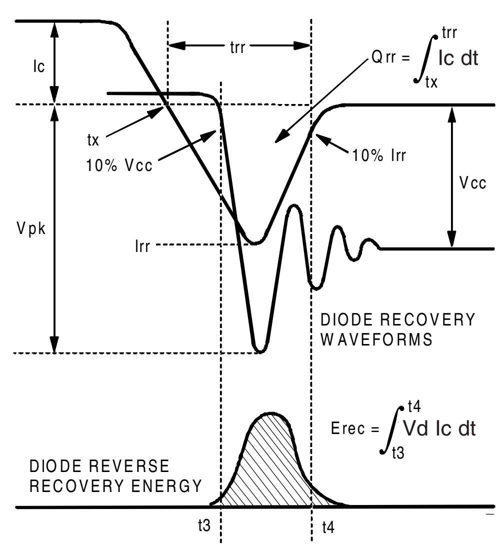


Fig. 18d - Test Waveforms for Circuit of Fig. 18a, Defining E_{rec}, t_{rr}, Q_{rr}, I_{rr}

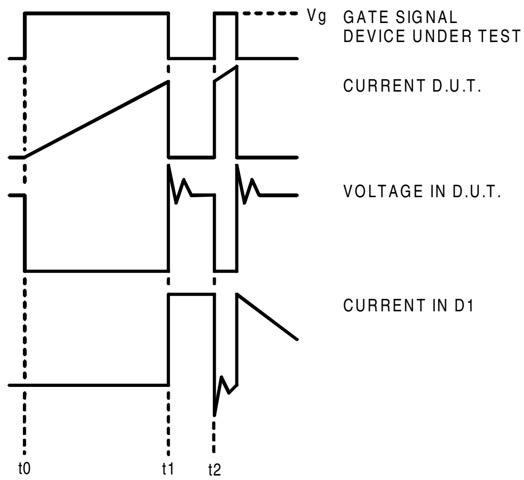


Figure 18e. Macro Waveforms for Figure 18a's Test Circuit

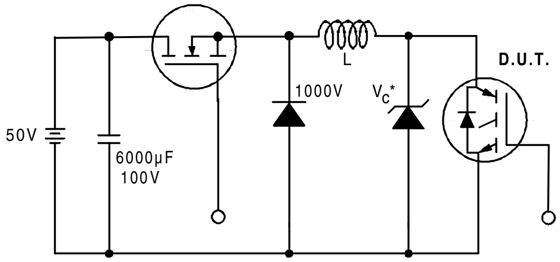


Figure 19. Clamped Inductive Load Test Circuit

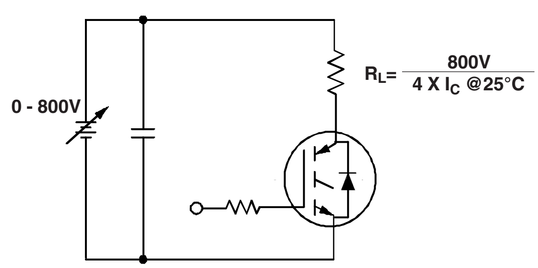


Figure 20. Pulsed Collector Current Test Circuit

Notes:

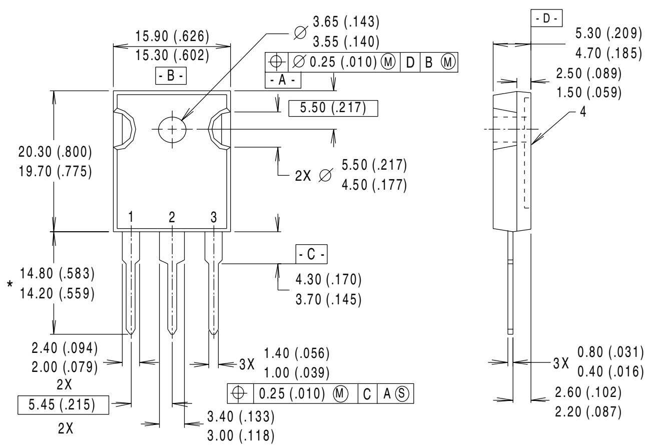
① Repetitive rating: V_{GE}=20V; pulse width limited by maximum junction temperature (figure 20)

② V_{CC}=80%(V_{CES}), V_{GE}=20V, L=10µH, R_G= 10Ω (figure 19)

③ Pulse width ≤ 80µs; duty factor ≤ 0.1%.

④ Pulse width 5.0µs, single shot.

Case Outline — TO-247AC



NOTES:
1 DIMENSIONS & TOLERANCING PER ANSI Y14.5M, 1982.
2 CONTROLLING DIMENSION : INCH.
3 DIMENSIONS ARE SHOWN MILLIMETERS (INCHES).
4 CONFORMS TO JEDEC OUTLINE TO-247AC.

LEAD ASSIGNMENTS
1 - GATE
2 - COLLECTOR
3 - EMITTER
4 - COLLECTOR

* LONGER LEADED (20mm) VERSION AVAILABLE (TO-247AD) TO ORDER ADD "-E" SUFFIX TO PART NUMBER

CONFORMS TO JEDEC OUTLINE TO-247AC (TO-3P)
Dimensions in Millimeters and (Inches)

International IOR Rectifier

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IR ITALY: Via Liguria 49, 10071 Borgaro, Torino Tel: ++ 39 011 451 0111
IR JAPAN: K&H Bldg., 2F, 30-4 Nishi-Ikebukuro 3-Chome, Toshima-Ku, Tokyo 171 Tel: 81 (0)3 3983 0086
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Note: For the most current drawings please refer to the IR website at:
http://www.irf.com/package/